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LMH6723/LMH6724/LMH6725 Single/Dual/Quad 370 MHz 1 mA Current Feedback **Operational Amplifier General Description**

The LMH6723/LMH6724/LMH6725 provides a 260 MHz small signal bandwidth at a gain of +2 V/V and a 600 V/ μ s slew rate while consuming only 1 mA from ±5V supplies.

The LMH6723/LMH6724/LMH6725 supports video applications with its 0.03% and 0.11° differential gain and phase for NTSC and PAL video signals. The LMH6723/LMH6724/ LMH6725 also offers a flat gain response of 0.1 dB to 100 MHz. Additionally, the LMH6723/LMH6724/LMH6725 can deliver 110 mA of linear output current. This level of performance, as well as a wide supply range of 4.5 to 12V, makes the LMH6723/LMH6724/LMH6725 an ideal op amp for a variety of portable applications. The LMH6723/LMH6724/ LMH6725's small packages (TSSOP, SOIC & SOT23), low power requirement and high performance allow the LMH6723/LMH6724/LMH6725 to serve a wide variety of portable applications.

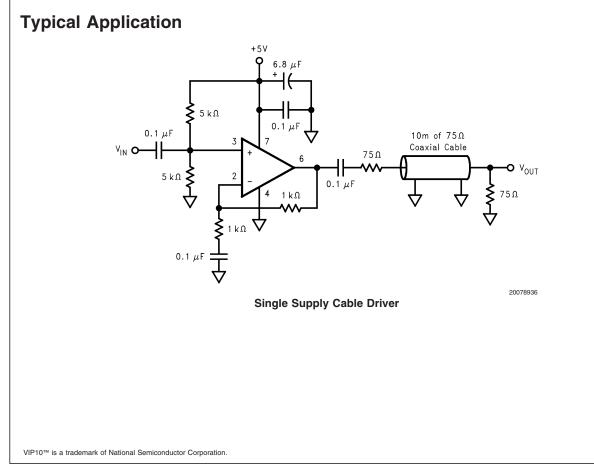
The LMH6723/LMH6724/LMH6725 is manufactured in National's VIP10™ complimentary bipolar process.

Features

- Large signal bandwidth and slew rate 100% tested
- 370 MHz bandwidth ($A_V = 1$, $V_{OUT} = 0.5 V_{PP}$) -3 dB BW
- 260 MHz (A_V = +2 V/V, V_{OUT} = 0.5 V_{PP}) -3 dB BW
- 1 mA supply current
- 110 mA linear output current
- 0.03%, 0.11° differential gain, phase
- 0.1 dB gain flatness to 100 MHz
- Fast slew rate: 600 V/µs
- Unity gain stable
- Single supply range of 4.5 to 12V
- Improved replacement for CLC450, CLC452, (LMH6723)

Applications

- Line driver
- Portable video
- A/D driver
- Portable DVD



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

V _{CC} (V ⁺ - V ⁻)	±6.75V
l _{out}	120 mA (Note 3)
Common Mode Input Voltage	$\pm V_{CC}$
Maximum Junction Temperature	+150°C
Storage Temperature Range	–65°C to +150°C
Soldering Information	
Infrared or Convection (20 sec)	235°C
Wave Soldering (10 sec)	260°C
ESD Tolerance (Note 4)	

Human Body Model 2000V Machine Model (Note 4)

200V

Operating Ratings (Note 3)

Thermal Resistance	
Package	(θ_{JA})
8-Pin SOIC	166°C/W
5-Pin SOT23	230°C/W
14-Pin SOIC	130°C/W
14-Pin TSSOP	160°C/W
Operating Temperature Range	–40°C to +85°C
Nominal Supply Voltage	4.5V to 12V

±5V Electrical Characteristics

Unless otherwise specified, $A_V = +2$, $R_F = 1200\Omega$, $R_L = 100\Omega$. **Boldface** limits apply at temperature extremes. (Note 2)

Parameter	Conditions		Min	Тур	Max	Units
cy Domain Response					•	
-3 dB Bandwidth Small Signal	$V_{OUT} = 0.5 V_{PP}$			260		MHz
-3dB Bandwidth Large Signal	$V_{OUT} = 4.0 V_{PP}$	LMH6723	90	110		
		LMH6724	85	95		MHz
		LMH6725				
-3 dB Bandwidth Unity Gain	$V_{OUT} = .2 V_{PP} A_V = 1$	1 V/V		370		MHz
.1 dB Bandwidth	$V_{OUT} = 0.5 V_{PP}$			100		MHz
Differential Gain	$R_{L} = 150\Omega, 4.43 \text{ MHz}$	z		0.03		%
Differential Phase	$R_{L} = 150\Omega, 4.43 \text{ MHz}$	z		0.11		deg
main Response						
Rise and Fall Time	4V Step			2.5		ns
Settling Time to 0.05%	2V Step			30		ns
Slew Rate	4V Step		500	600		V/µs
n and Noise Response						
2 nd Harmonic Distortion	2 V _{PP} , 5 MHz	2 V _{PP} , 5 MHz		-65		dBc
3 rd Harmonic Distortion	2 V _{PP} , 5 MHz			-63		dBc
nt Input Noise						
Non-Inverting Voltage Noise	>1 MHz			4.3		nV/√H:
Inverting Current Noise	>1 MHz	>1 MHz		6		pA/√H
Non-Inverting Current Noise	>1 MHz	>1 MHz		6		pA/√H:
C Performance						
Input Offset Voltage				1	±3	mV
					±3.7	
Input Bias Current	Non-Inverting			-2	±4	μA
					±5	µ, (
Input Bias Current	Inverting			0.4	±4	μΑ
					±5	r -
Power Supply Rejection Ratio	DC, 1V Step	LMH6723		64		
						4
		LMH6724		64		dB
		1 10705				-
		LMH6725		64		
Power Sup	ply Rejection Ratio	ply Rejection Ratio DC, 1V Step	ply Rejection Ratio DC, 1V Step LMH6723 LMH6724 LMH6725	57 LMH6724 59 55	57 LMH6724 59 64 55 55 LMH6725 59 64	57 57 LMH6724 59 64 55 55 LMH6725 59 64

	therwise specified, $A_V = +2$, $R_F =$						-/
Symbol	Parameter	Conditio	ns	Min	Тур	Max	Units
CMRR Con	Common Mode Rejection Ratio	mon Mode Rejection Ratio DC, 1V Step	LMH6723	57 55	60		
			LMH6724	57 53	60		dB
			LMH6725	57 54	60		
I _{CC}	Supply Current (per amplifier)	R _L = ∞			1	1.2 1.4	mA
Miscellane	eous Performance						
R _{IN+}	Input Resistance	Non-Inverting			100		kΩ
R _{IN-}	Input Resistance (Output Resistance of Input Buffer)	Inverting			500		Ω
CIN	Input Capacitance	Non-Inverting			1.5		pF
R _{OUT}	Output Resistance	Closed Loop			0.01		Ω
Vo	Output Voltage Range	R _L = ∞	LMH6723	±4 ±3.9	±4.1		v
		LMH6724 LMH6725	±4 ±3.85	±4.1			
V _{OL}	Output Voltage Range, High	R _L = 100Ω		3.6 3.5	3.7		v
	Output Voltage Range, Low	R _L = 100Ω		-3.25 -3.1	-3.45		
CMVR	Input Voltage Range			±4.0			V
lo	Output Current	Sourcing, $V_{OUT} = 0$		95 70	110		mA
		Sinking, V _{OUT} = 0		-80 -70	110		– mA

±2.5V Electrical Characteristics

Unless otherwise specified, $A_V = +2$, $R_F = 1200\Omega$, $R_L = 100\Omega$. **Boldface** limits apply at temperature extremes. (Note 2)

Symbol	Parameter	Conditie	ons	Min	Тур	Max	Units
Frequency	Domain Response	•	1				
SSBW	-3 dB Bandwidth Small Signal	$V_{OUT} = 0.5 V_{PP}$			210		MHz
LSBW	-3 dB Bandwidth Large Signal		95	125			
			LMH6724 LMH6725	90	100		MHz
UGBW	-3 dB Bandwidth Unity Gain	$V_{OUT} = 0.5 V_{PP}, A_V =$	$V_{OUT} = 0.5 V_{PP}, A_V = 1 V/V$		290		MHz
.1dB BW	.1 dB Bandwidth	$V_{OUT} = 0.5 V_{PP}$	$V_{OUT} = 0.5 V_{PP}$		100		MHz
DG	Differential Gain	R _L = 150Ω, 4.43 MHz			.03		%
DP	Differential Phase	$R_{L} = 150\Omega, 4.43 \text{ MHz}$			0.1		deg
Time Dom	ain Response						
TRS	Rise and Fall Time	2V Step			4		ns
SR	Slew Rate	2V Step		275	400		V/µs
Distortion	and Noise Response						
HD2	2 nd Harmonic Distortion	2 V _{PP} , 5 MHz			-67		dBc
HD3	3 rd Harmonic Distortion	2 V _{PP} , 5 MHz			-67		dBc
Equivalen	Input Noise	•					·
VN	Non-Inverting Voltage	>1 MHz			4.3		nV/ √Hz

LMH6723/LMH6724/LMH6725

Symbol	Parameter	Conditi	ons	Min	Тур	Max	Units	
NICN	Inverting Current	>1MHz			6	-	pA/ √Hz	
ICN	Non-Inverting Current	>1MHz			6		pA/ √Hz	
Static, DC	Performance	I					1.	
V _{IO}	Input Offset Voltage				-0.5	±3		
						±3.4	mV	
I _{BN}	Input Bias Current	Non-Inverting			-2.7	±4 ±5	μA	
I _{BI}	Input Bias Current	Inverting			-0.7	±4 ±5	μΑ	
PSRR	Power Supply Rejection Ratio	DC, 0.5V Step	LMH6723	59 57	62			
			LMH6724	58 55	62		dB	
			LMH6725	59 56	62		-	
CMRR Common Mode Rejection Ratio	DC, 0.5V Step	LMH6723	57 53	59				
		LMH6724	55 52	59		dB		
			LMH6725	57 52	59		1	
Icc	Supply Current (per amplifier)	R _L = ∞			.9	1.1 1.3	mA	
Miscellan	eous Performance							
R _{IN+}	Input Resistance	Non-Inverting			100		kΩ	
R _{IN-}	Input Resistance (Output Resistance of Input Buffer)	Inverting			500		Ω	
C _{IN}	Input Capacitance	Non-Inverting			1.5		pF	
R _{OUT}	Output Resistance	Closed Loop			.02		Ω	
Vo	Output Voltage Range	R _L = ∞		±1.55 ±1.4	±1.65		V	
V _{OL}	Output Voltage Range, High	$R_L = 100\Omega$	LMH6723	1.35 1.27	1.45			
			LMH6724 LMH6725	1.35 1.26	1.45		V	
	Output Voltage Range, Low	/oltage Range, Low $R_L = 100\Omega$ LMH	LMH6723	-1.25 -1.15	-1.38			
			LMH6724 LMH6725	-1.25 -1.15	-1.38		- V	
CMVR	Input Voltage Range	Common Mode, CMR	R > 50 dB	±1.45			V	
lo	Output Current	Sourcing		70 60	90		A	
		Sinking		-30 -30	-60		- mA	

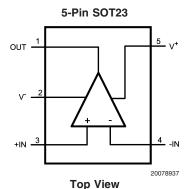
Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications, see the Electrical Characteristics tables.

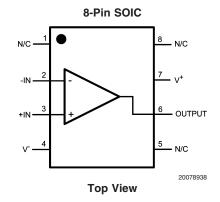
Note 2: Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No guarantee of parametric performance is indicated in the electrical tables under conditions of internal self heating where $T_J > T_A$. See Applications Section for information on temperature derating of this device. Min/Max ratings are based on product characterization and simulation. Individual parameters are tested as noted.

Note 3: The maximum continuous output current (I_{OUT}) is determined by device power dissipation limitations. See the Power Dissipation section of the Application Section for more details.

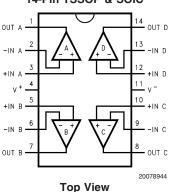
Note 4: Human Body Model, 1.5 k Ω in series with 100 pF. Machine Model, 0 Ω In series with 200 pF.

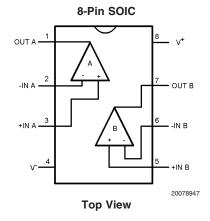
Connection Diagrams





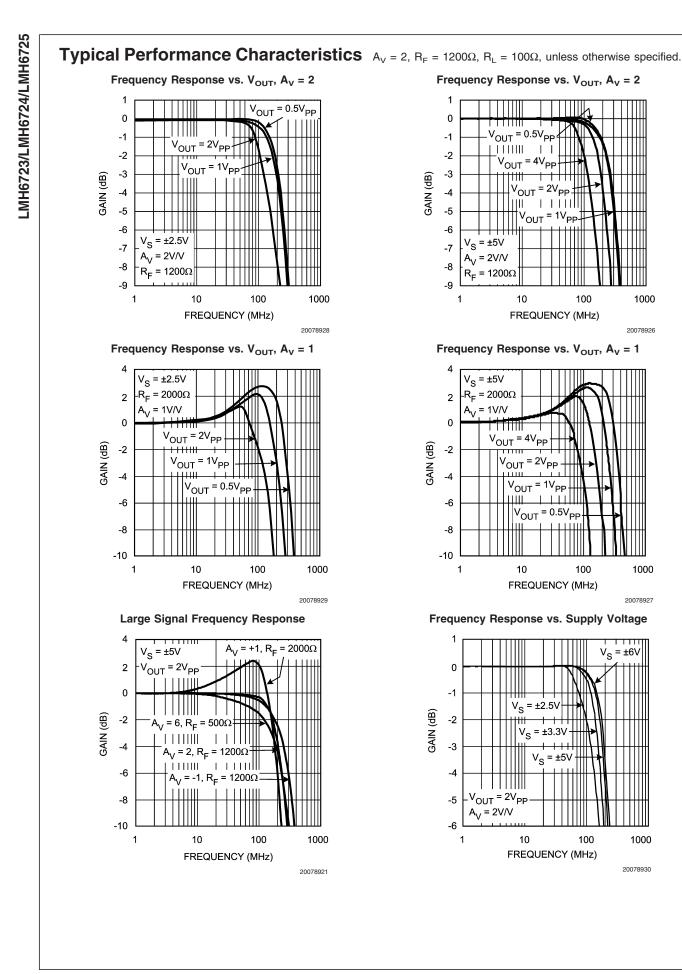






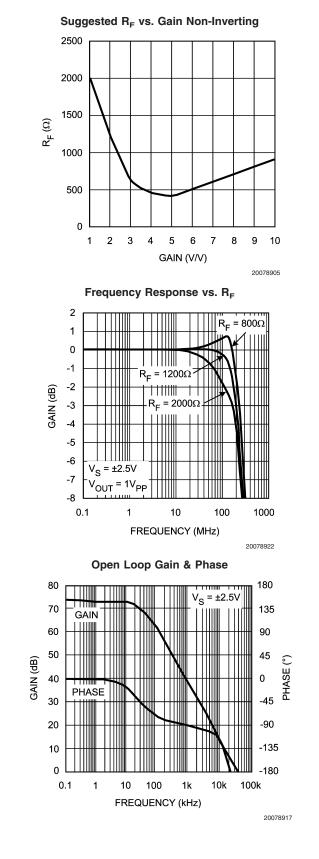
Ordering Information

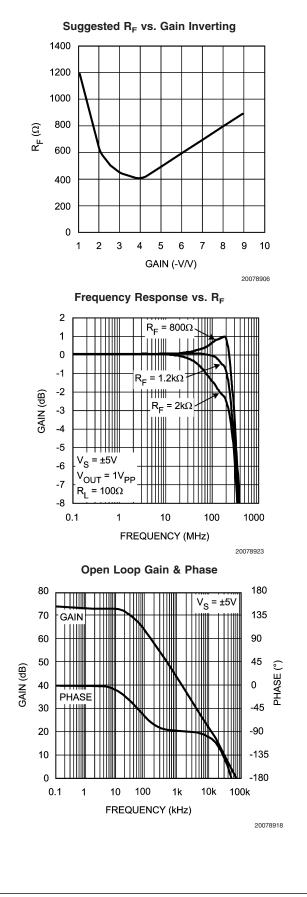
Package	Part Number	Package Marking	Transport Media	NSC Drawing
5-Pin SOT23	LMH6723MF	AB1A	1k Units Tape and Reel	MF05A
5-PIII 50125	LMH6723MFX	ADIA	3k Units Tape and Reel	
	LMH6723MA		95 Units/Rail	M08A
8-Pin SOIC LMH6723MAX LMH6723MA		2.5k Units Tape and Reel	INIOA	
8-Pin SOIC	LMH6724MA	LMH6724MA	95 Units/Rail	M08A
0-FIII 3010	LMH6724MAX		2.5k Units Tape and Reel	INIUOA
14-Pin SOIC	LMH6725MA	LMH6725MA	55 Units/Rail	M14A
LMH6725MAX			2.5k Units Tape and Reel	IVIT4A
14-Pin TSSOP	LMH6725MT LMH6725MT		94 Units/Rail	MTC14
LMH6725MTX			2.5k Units Tape and Reel	WITC14

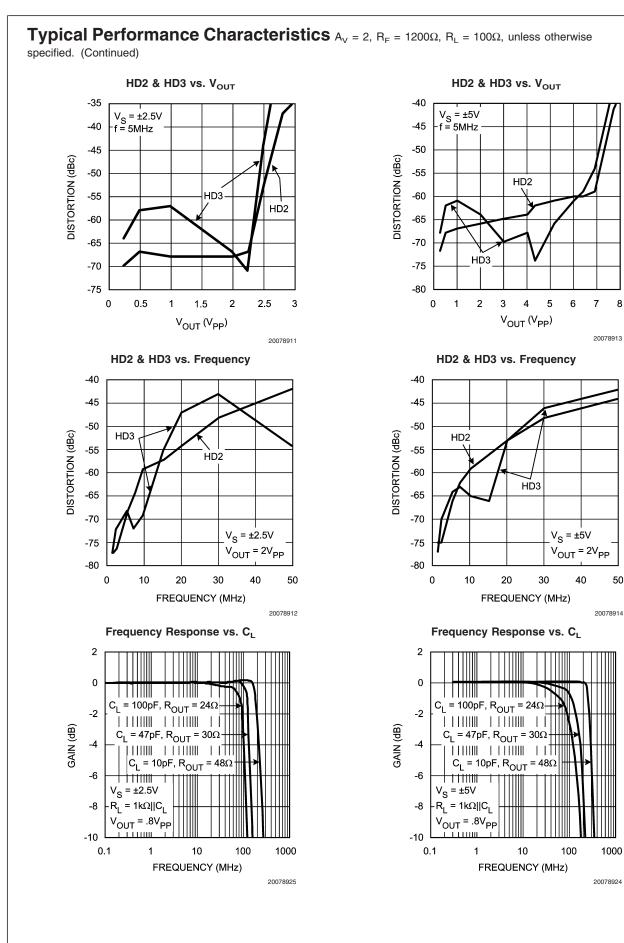


Typical Performance Characteristics $A_V = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise

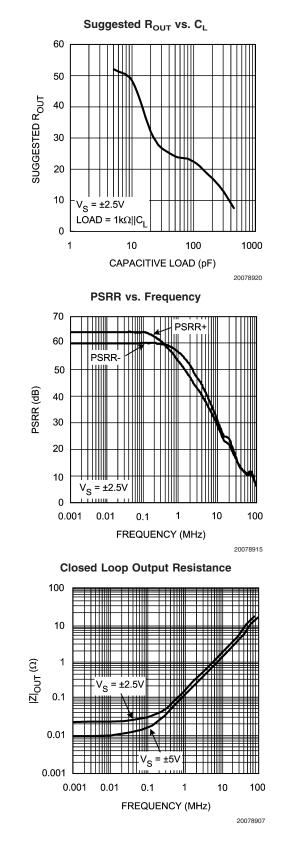
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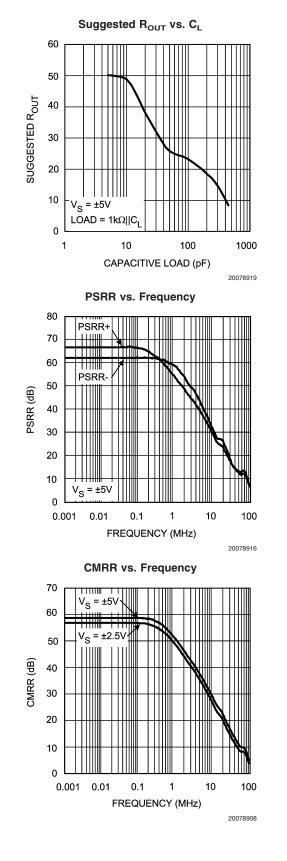


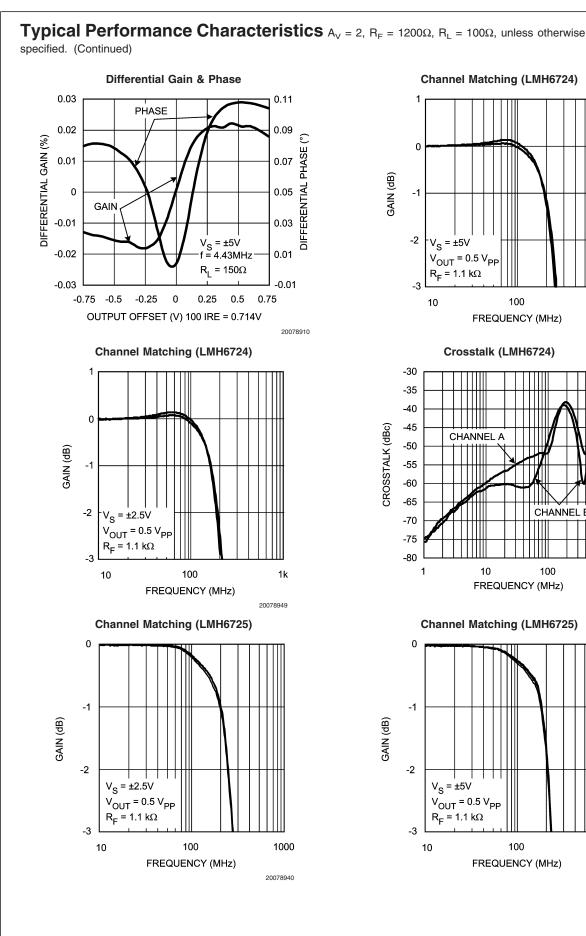


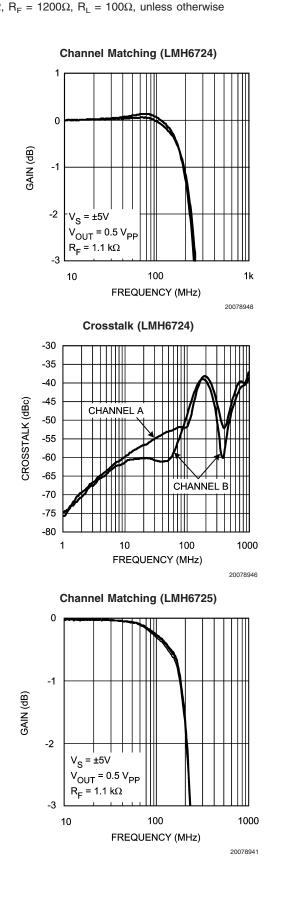


Typical Performance Characteristics $A_V = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise specified. (Continued)

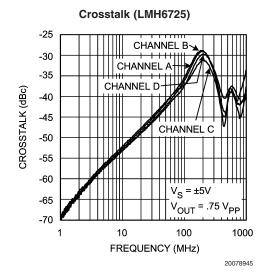








Typical Performance Characteristics $A_v = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise specified. (Continued)



Application Section

GENERAL INFORMATION

The LMH6723/LMH6724/LMH6725 is a high speed current feedback amplifier manufactured on National Semiconductor's VIP10 (Vertically Integrated PNP) complimentary bipolar process. LMH6723/LMH6724/LMH6725 offers a unique combination of high speed and low quiescent supply current making it suitable for a wide range of battery powered and portable applications that require high performance. This amplifier can operate from 4.5V to 12V nominal supply voltages and draws only 1 mA of quiescent supply current at 10V supplies (±5V typically). The LMH6723/LMH6724/LMH6725 has no internal ground reference so single or split supply configurations are both equally useful.

EVALUATION BOARDS

National Semiconductor provides the following evaluation boards as a guide for high frequency layout and as an aid in device testing and characterization. Many of the datasheet plots were measured with these boards.

Device	Package	Board Part #
LMH6723MA	SOIC-8	CLC730227
LMH6723MF	SOT-23	CLC730216
LMH6724MA	SOIC-8	CLC730036
LMH6725MA	SOIC-14	CLC730231

These evaluation boards can be shipped when a device sample request is placed with National Semiconductor.

FEEDBACK RESISTOR SELECTION

One of the key benefits of a current feedback operational amplifier is the ability to maintain optimum frequency response independent of gain by using appropriate values for the feedback resistor (R_F). The Electrical Characteristics and Typical Performance plots were generated with an R_F of 1200 Ω , a gain of +2V/V and ±5V or ±2.5V power supplies (unless otherwise specified). Generally, lowering R_F from it's recommended value will peak the frequency response and extend the bandwidth; however, increasing the value of R_F

will cause the frequency response to roll off faster. Reducing the value of ${\sf R}_{\sf F}$ too far below it's recommended value will cause overshoot, ringing and, eventually, oscillation.

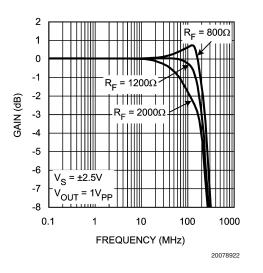


FIGURE 1. Frequency Response vs. R_F

Figure 1 shows the LMH6723/LMH6724/LMH6725's frequency response as R_F is varied (R_L = 100 Ω , A_V = +2). This plot shows that an R_F of 800 Ω results in peaking. An R_F of 1200 Ω gives near maximal bandwidth and gain flatness with good stability. Since each application is slightly different it is worth some experimentation to find the optimal R_F for a given circuit. In general a value of R_F that produces ~0.1 dB of peaking is the best compromise between stability and maximal bandwidth. Note that it is not possible to use a current feedback amplifier with the output shorted directly to the inverting input. The buffer configuration of the LMH6723/LMH6724/LMH6725 requires a 2000 Ω feedback resistor for stable operation. For other gains see the charts "R_F vs. Non

Application Section (Continued)

Inverting Gain" and " R_F vs. Inverting Gain". These charts provide a good place to start when selecting the best feedback resistor value for a variety of gain settings.

For more information see Application Note OA-13 which describes the relationship between $\rm R_F$ and closed-loop frequency response for current feedback operational amplifiers. The value for the inverting input impedance for the LMH6723/LMH6724/LMH6725 is approximately 500 Ω . The LMH6723/LMH6724/LMH6725 is designed for optimum performance at gains of +1 to +5V/V and -1 to -4V/V. Higher gain configurations are still useful; however, the bandwidth will fall as gain is increased, much like a typical voltage feedback amplifier.

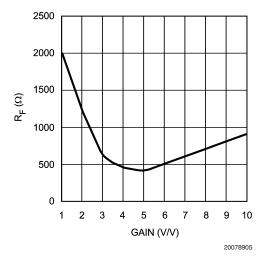


FIGURE 2. RF vs. Non-Inverting Gain

Figure 2 and Figure 3 show the value of $R_{\rm F}$ versus gain. A higher $R_{\rm F}$ is required at higher gains to keep $R_{\rm G}$ from decreasing too far below the input impedance of the inverting input. This limitation applies to both inverting and non-inverting configurations. For the LMH6723/LMH6724/LMH6725 the input resistance of the inverting input is approximately 500 Ω and 100 Ω is a practical lower limit for $R_{\rm G}$. The LMH6723/LMH6724/LMH6725 begins to operate in a gain bandwidth limited fashion in the region where $R_{\rm F}$ must be increased for higher gains. Note that the amplifier will operate with $R_{\rm G}$ values well below 100 Ω ; however, results will be substantially different than predicted from ideal models. In particular, the voltage potential between the Inverting and Non-Inverting inputs cannot be expected to remain small.

For inverting configurations the impedance seen by the source is $R_G \parallel R_T$. For most sources this limits the maximum inverting gain since R_F is determined by the desired gain as shown in *Figure 3*. The value of R_G is then $R_F/Gain$. Thus for an inverting gain of -4 V/V the input impedance is equal to 100 Ω . Using a termination resistor, this can be brought down to match a 50 Ω or 75 Ω source; however, a 150 Ω source cannot be matched without a severe compromise in R_F .

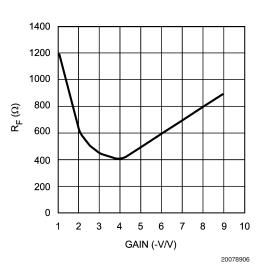


FIGURE 3. R_F vs. Inverting Gain

ACTIVE FILTERS

When using any current feedback operational amplifier as an active filter it is necessary to be careful using reactive components in the feedback loop. Reducing the feedback impedance, especially at higher frequencies, will almost certainly cause stability problems. Likewise capacitance on the inverting input should be avoided. See Application Notes OA-7 and OA-26 for more information on Active Filter applications for Current Feedback Op Amps.

When using the LMH6723/LMH6724/LMH6725 as a lowpass filter the value of R_F can be substantially reduced from the value recommended in the R_F vs. Gain charts. The benefit of reducing R_F is increased gain at higher frequencies, which improves attenuation in the stop band. Stability problems are avoided because in the stop band additional device bandwidth is used to cancel the input signal rather than amplify it. The benefit of this change depends on the particulars of the circuit design. With a high pass filter configuration reducing R_F will likely result in device instability and is not recommended.

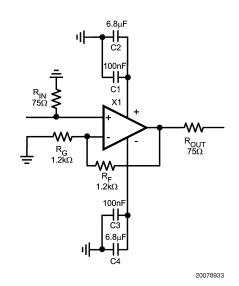


FIGURE 4. Typical Application with Suggested Supply Bypassing

Application Section (Continued)

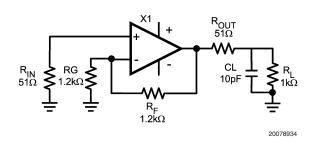


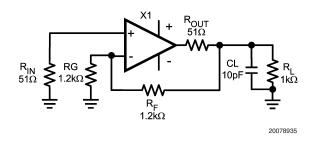
FIGURE 5. Decoupling Capacitive Loads

DRIVING CAPACITIVE LOADS

Capacitive output loading applications will benefit from the use of a series output resistor as shown in *Figure 5*. The charts "Suggested R_{OUT} vs. Cap Load" give a recommended value for selecting a series output resistor for mitigating capacitive loads. The values suggested in the charts are selected for .5 dB or less of peaking in the frequency response. This gives a good compromise between settling time and bandwidth. For applications where maximum frequency response is needed and some peaking is tolerable, the value of R_{OUT} can be reduced slightly from the recommended values.

There will be amplitude lost in the series resistor unless the gain is adjusted to compensate; this effect is most noticeable with heavy loads ($R_L < 150\Omega$).

An alternative approach is to place R_{OUT} inside the feedback loop as shown in *Figure 6*. This will preserve gain accuracy, but will still limit maximum output voltage swing.





INVERTING INPUT PARASITIC CAPACITANCE

Parasitic capacitance is any capacitance in a circuit that was not intentionally added. It is produced through electrical interaction between conductors and can be reduced but never entirely eliminated. Most parasitic capacitances that cause problems are related to board layout or lack of termination on transmission lines. Please see the section on Layout Considerations for hints on reducing problems due to parasitic capacitances on board traces. Transmission lines should be terminated in their characteristic impedance at both ends.

High speed amplifiers are sensitive to capacitance between the inverting input and ground or power supplies. This shows up as gain peaking at high frequency. The capacitor raises device gain at high frequencies by making R_G appear smaller. Capacitive output loading will exaggerate this effect.

One possible remedy for this effect is to slightly increase the value of the feedback (and gain set) resistor. This will tend to offset the high frequency gain peaking while leaving other parameters relatively unchanged. If the device has a capacitive load as well as inverting input capacitance, using a series output resistor as described in the section on "Driving Capacitive Loads" will help.

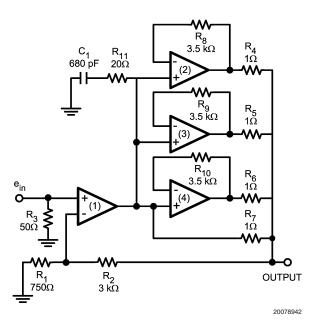


FIGURE 7. High Output Current Composite Amplifier

When higher currents are required than a single amplifier can provide, the circuit of *Figure 7* can be used. Although the example circuit was intended for the LMH6725 quad op amp, higher thermal efficiency can be obtained by using four separate SOIC op amps. Careful attention to a few key components will optimize performance from this circuit. The first thing to note is that the buffers need slightly higher value feedback resistors than if the amplifiers were individually configured. As well, R_{11} and C_1 provide mid circuit frequency compensation to further improve stability. The composite amplifier has approximately twice the phase delay of a single circuit. The larger values of R_8 , R_9 and R_{10} , as well as the high frequency attenuation provided by C_1 and R_{11} , ensure that the circuit does not oscillate.

Resistors R_4 , R_5 , R_6 , and R_7 are necessary to ensure even current distribution between the amplifiers. Since they are inside the feedback loop they have no effect on the gain of the circuit. The circuit shown in *Figure 7* has a gain of 5. The frequency response of this circuit is shown in *Figure 8*.

Application Section (Continued)

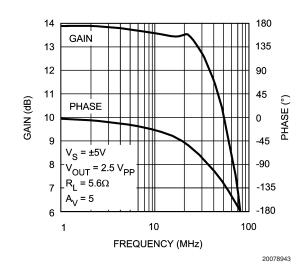


FIGURE 8. Composite Amplifier Frequency Response

LAYOUT CONSIDERATIONS

Whenever questions about layout arise, use the evaluation board as a guide. Evaluation boards are shipped with sample requests.

To reduce parasitic capacitances ground and power planes should be removed near the input and output pins. Components in the feedback loop should be placed as close to the device as possible. For long signal paths controlled impedance lines should be used, along with impedance matching at both ends.

Bypass capacitors should be placed as close to the device as possible. Bypass capacitors from each rail to ground are applied in pairs. The larger electrolytic bypass capacitors can be located anywhere on the board; however, the smaller ceramic capacitors should be placed as close to the device as possible.

VIDEO PERFORMANCE

The LMH6723/LMH6724/LMH6725 has been designed to provide good performance with both PAL and NTSC composite video signals. The LMH6723/LMH6724/LMH6725 is specified for PAL signals. Typically, NTSC performance is marginally better due to the lower frequency content of the signal. Performance degrades as the loading is increased;

therefore, best performance will be obtained with back terminated loads. The back termination reduces reflections from the transmission line and effectively masks transmission line and other parasitic capacitances from the amplifier output stage. *Figure 4* shows a typical configuration for driving a 75 Ω cable. The amplifier is configured for a gain of 2 to make up for the 6dB of loss in R_{OUT}.

SINGLE 5V SUPPLY VIDEO

With a 5V supply the LMH6723/LMH6724/LMH6725 is able to handle a composite NTSC video signal, provided that the signal is AC coupled and level shifted so that the signal is centered around $V_{\rm CC}/2$.

POWER DISSIPATION

Follow these steps to determine the maximum power dissipation for the LMH6723/LMH6724/LMH6725:

- 1. Calculate the quiescent (no-load) power: P_{AMP} = I_CC * (V_S) V_S = V^+ V^-
- 2. Calculate the RMS power dissipated in the output stage: P_D (rms) = rms ((V_S-V_{OUT})*I_{OUT}) where V_{OUT} and I_{OUT} are the voltage and current across the external load and V_S is the total supply current.
- 3. Calculate the total RMS power: $P_T = P_{AMP} + P_D$

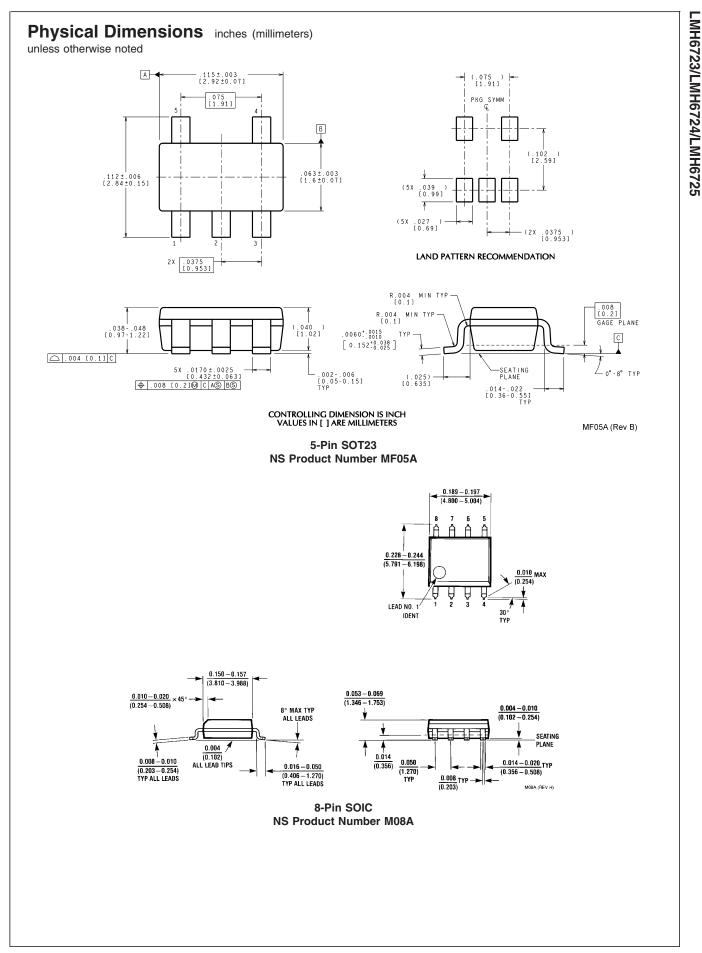
The maximum power that the LMH6723/LMH6724/LMH6725 package can dissipate at a given temperature can be derived with the following equation:

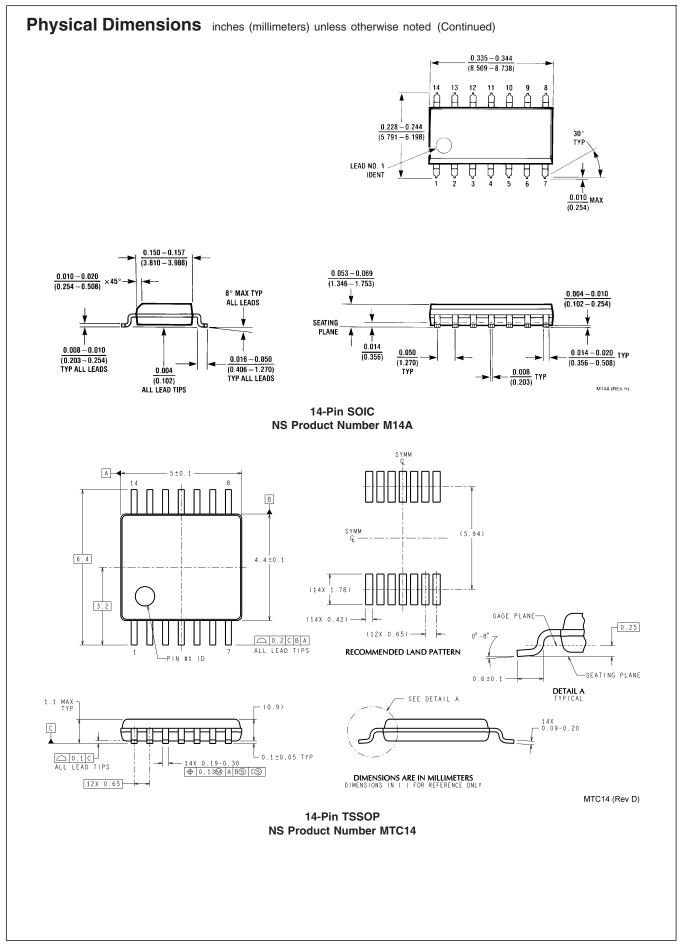
 P_{MAX} = (150° - $T_{AMB})/$ θ_{JA} , where T_{AMB} = Ambient temperature (°C) and θ_{JA} = Thermal resistance, from junction to ambient, for a given package (°C/W). For the SOIC-8 package θ_{JA} is 166°C/W and for the SOT it is 230°C/W. The SOIC-14 has a θ_{JA} of 130°C/W. The TSSOP-14 has a θ_{JA} of 160°C/W.

ESD PROTECTION

The LMH6723/LMH6724/LMH6725 is protected against electrostatic discharge (ESD) on all pins. The LMH6723/ LMH6725 will survive 2000V Human Body Model or 200V Machine Model events.

Under closed loop operation the ESD diodes have no effect on circuit performance. There are occasions, however, when the ESD diodes will be evident. If the LMH6723/LMH6724/ LMH6725 is driven into a slewing condition the ESD diodes will clamp large differential voltages until the feedback loop restores closed loop operation. Also, if the device is powered down and a large input signal is applied, the ESD diodes will conduct.





Notes

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